

P-Channel Trench Power MOSFET

General Description

The CSP40P150 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

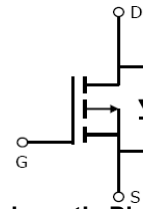
Features

- $V_{DS} = -40V, I_D = -8A$
 $R_{DS(ON)} < 21m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 31m\Omega @ V_{GS} = -4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

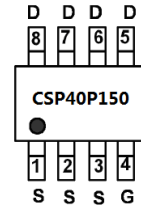
Application

- DC-DC converter
- Load switch
- Power management

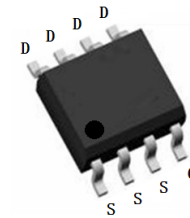
100% UIS TESTED!



Schematic Diagram



Marking and pin Assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
CSP40P150	CSP40P150	SOP-8	Ø330mm	12mm	2500 units

Table 1. Absolute Maximum Ratings ($T_A=25^\circ C$)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	-40	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^\circ C$)	-8	A
	Drain Current-Continuous($T_C=100^\circ C$)	-5	A
$I_{DM (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	-32	A
P_D	Maximum Power Dissipation($T_C=25^\circ C$)	3	W
	Maximum Power Dissipation($T_C=100^\circ C$)	1.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$

Table 2. Thermal Characteristic

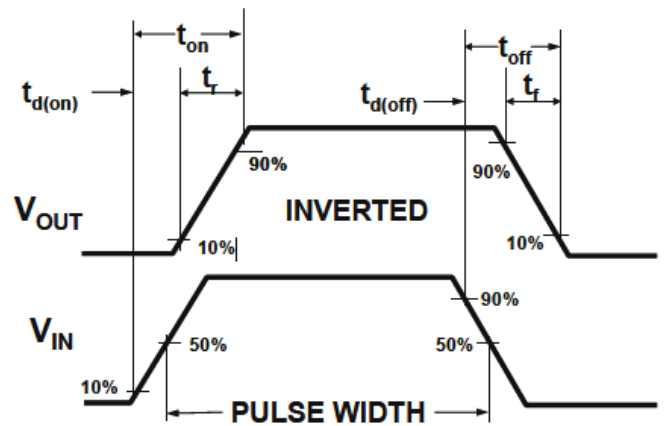
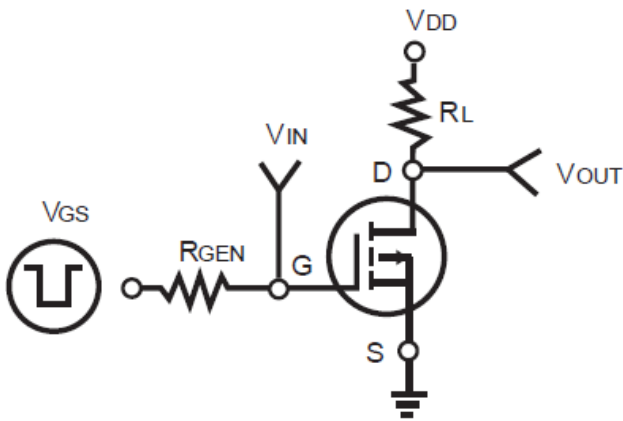
Symbol	Parameter	Typ	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	42	$^\circ C/W$

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-40V, V _{GS} =0V			-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.1	-1.7	-2.5	V
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-5A	15			S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-8A		16	21	mΩ
		V _{GS} =-4.5V, I _D =-5A		21	31	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1.0MHz		2050		pF
C _{oss}	Output Capacitance			260		pF
C _{rss}	Reverse Transfer Capacitance			150		pF
Switching Times						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-20V, R _L =1.6Ω, R _{GEN} =3Ω		10		nS
t _r	Turn-on Rise Time			24		nS
t _{d(off)}	Turn-Off Delay Time			40		nS
t _f	Turn-Off Fall Time			9		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-20V, I _D =-8A		45		nC
Q _{gs}	Gate-Source Charge			6		nC
Q _{gd}	Gate-Drain Charge			11		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current(Body Diode)				-8	A
V _{SD}	Forward on Voltage	V _{GS} =0V, I _S =-8A			-1.2	V

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

Switch Time Test Circuit and Switching Waveforms:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Power Dissipation

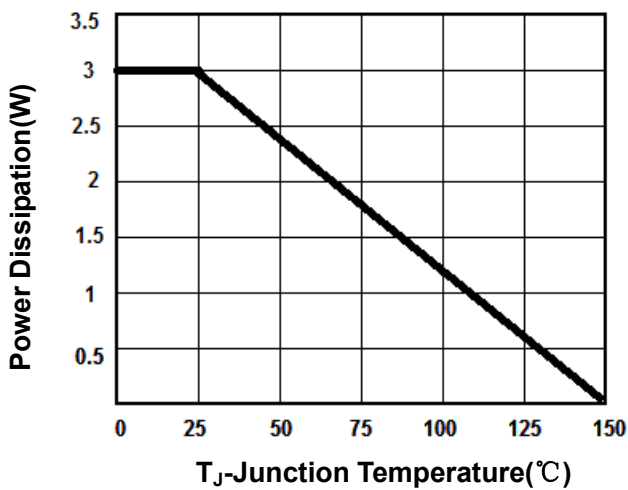


Figure2. Drain Current

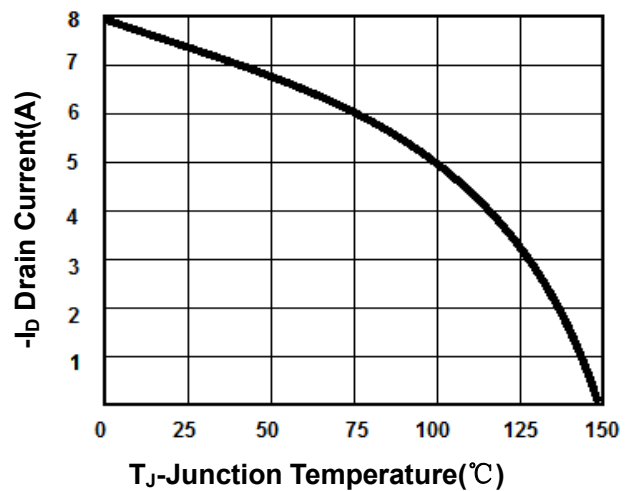


Figure3. Output Characteristics

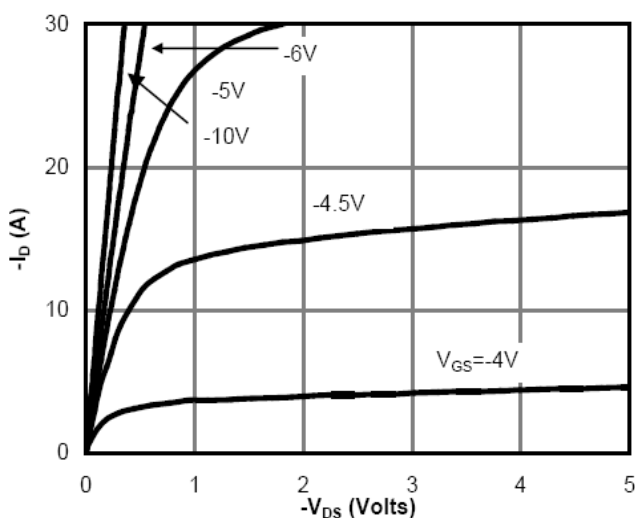


Figure4. Transfer Characteristics

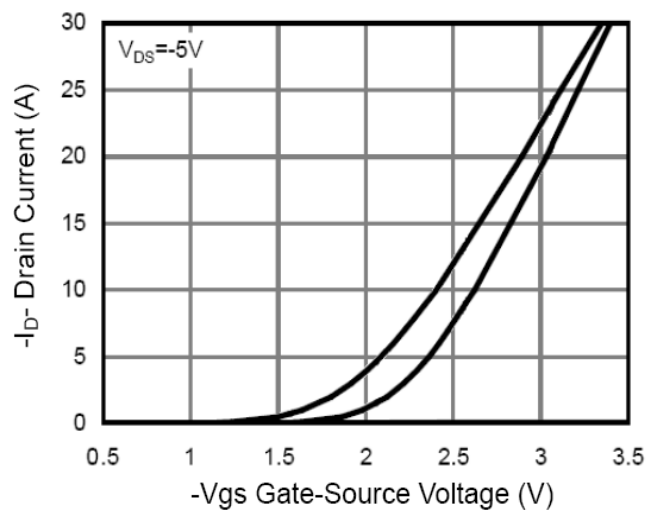


Figure5. Capacitance

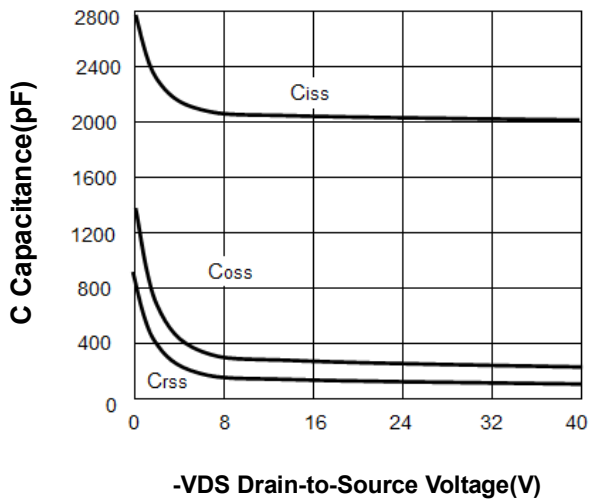


Figure6. $R_{DS(ON)}$ vs Junction Temperature

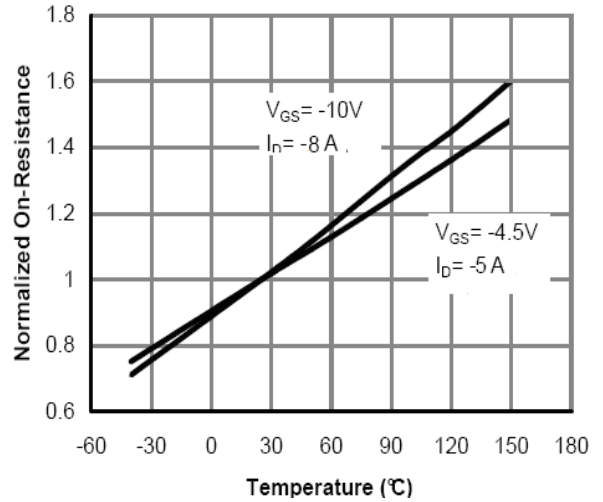


Figure7. $V_{GS(th)}$ vs Junction Temperature

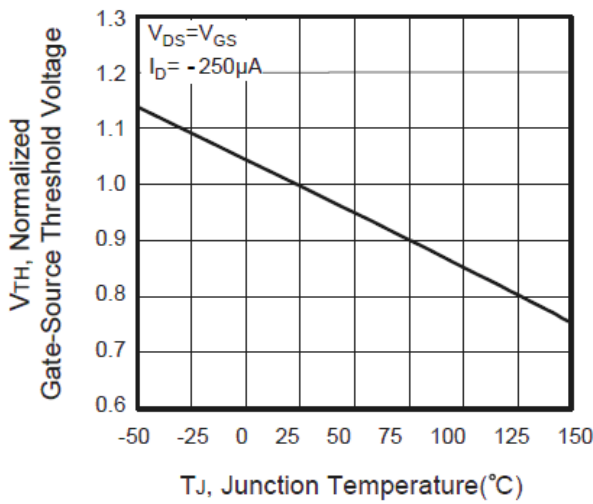


Figure8. Gate Charge Waveforms

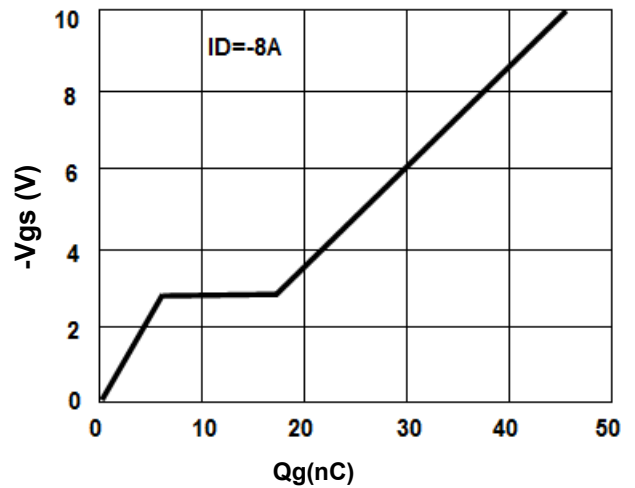
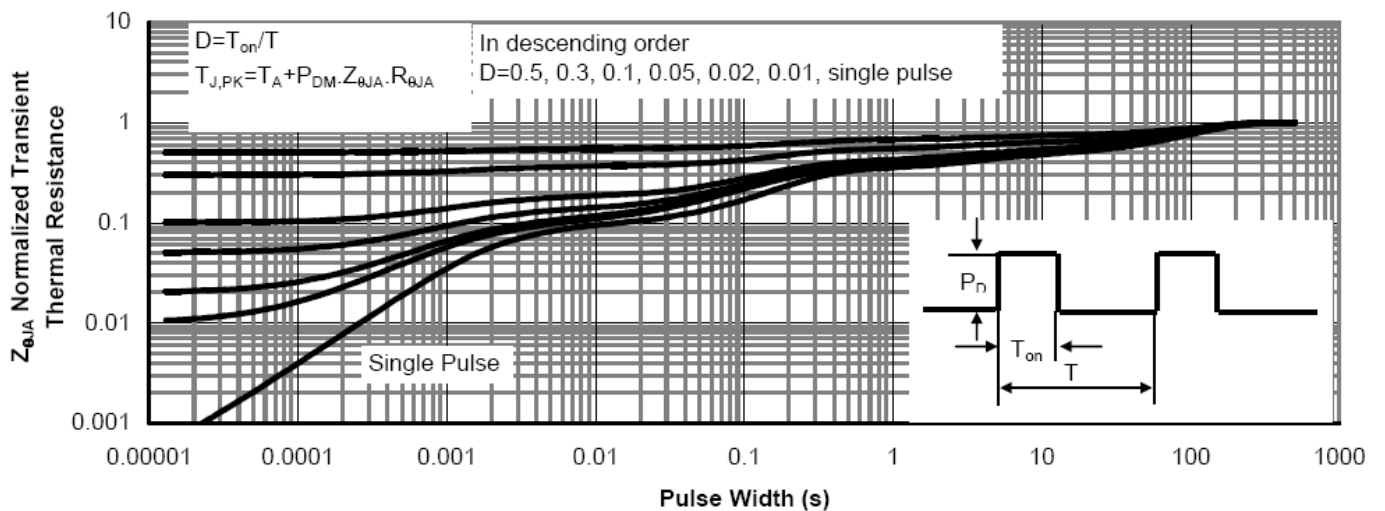
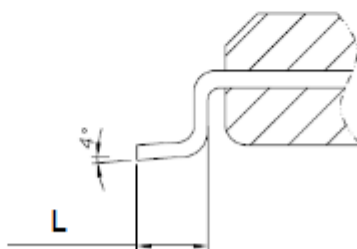
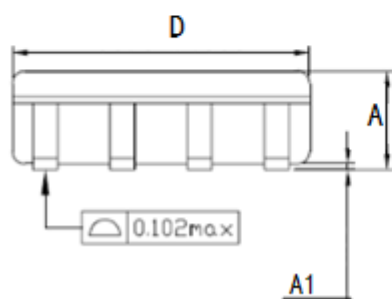
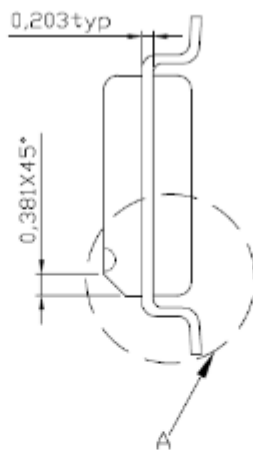
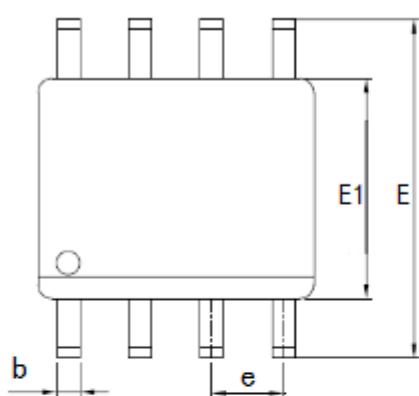


Figure9. Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



A 局部放大

COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.1	0.15	0.2
b	0.346	0.406	0.466
D	4.8	4.89	4.98
E	5.75	6.00	6.25
E1	3.81	3.90	3.99
e	1.27TYP		
L	0.406	0.838	1.27